



ALPHA & OMEGA
SEMICONDUCTOR

AO7407

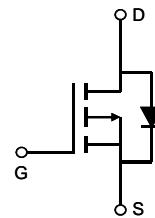
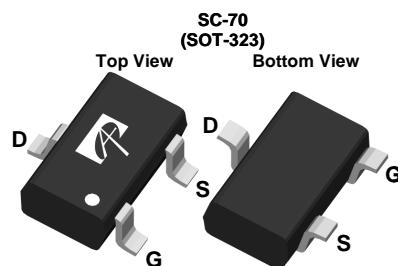
20V P-Channel MOSFET

General Description

The AO7407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{DS}	-20V
I_D (at $V_{GS}=-4.5V$)	-1.2A
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 135mΩ
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$)	< 170mΩ
$R_{DS(ON)}$ (at $V_{GS}=-1.8V$)	< 220mΩ



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-1.2	A
Current		-1	
Pulsed Drain Current ^C	I_{DM}	-10	
Power Dissipation ^B	P_D	0.63	W
		0.4	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	160	200	°C/W
Maximum Junction-to-Ambient ^{A/D}		180	220	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	130	160	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}= \pm 8\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.4	-0.65	-1	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-10			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}, I_D=-1.2\text{A}$ $T_J=125^\circ\text{C}$		65	135	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-1\text{A}$		90	175	
		$V_{GS}=-1.8\text{V}, I_D=-1\text{A}$		80	170	
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-1.2\text{A}$		100	220	mΩ
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$	-0.7	-1	-1	V
I_s	Maximum Body-Diode Continuous Current				-1	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$		560	745	pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		15	23.0	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-1.2\text{A}$		8.5	11	nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			2.1		nC
$t_{\text{D(on)}}$	Turn-On DelayTime	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, R_L=8.3\Omega, R_{\text{GEN}}=3\Omega$		7.2		ns
t_r	Turn-On Rise Time			36		ns
$t_{\text{D(off)}}$	Turn-Off DelayTime			53		ns
t_f	Turn-Off Fall Time			56		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-1.2\text{A}, dI/dt=100\text{A}/\mu\text{s}$		37	49	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-1.2\text{A}, dI/dt=100\text{A}/\mu\text{s}$		27		nC

A. The value of R_{gJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

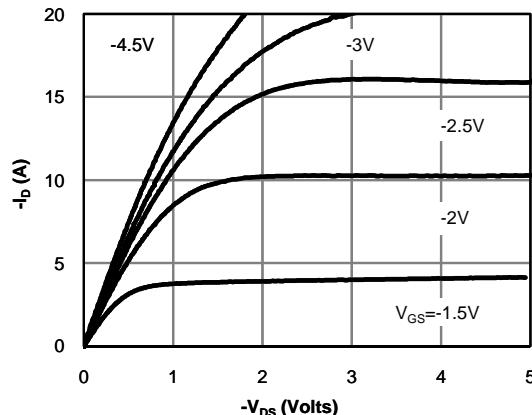
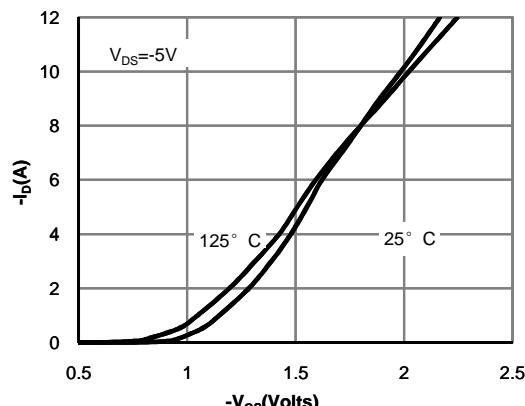
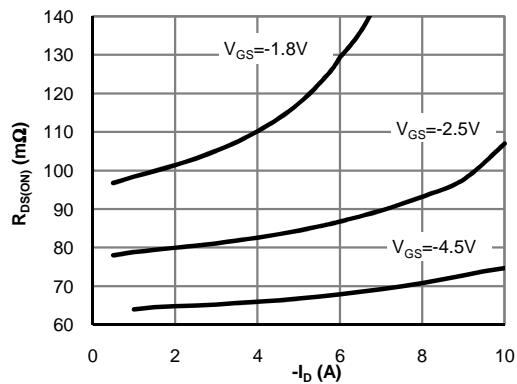
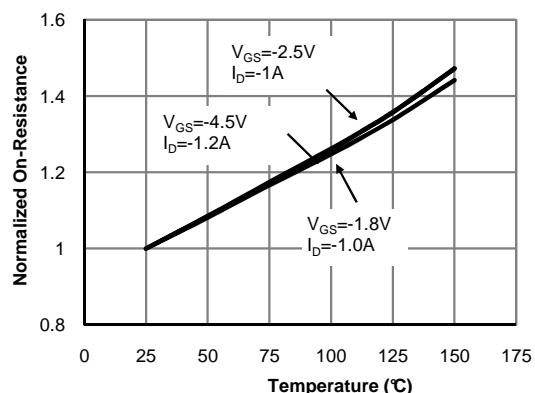
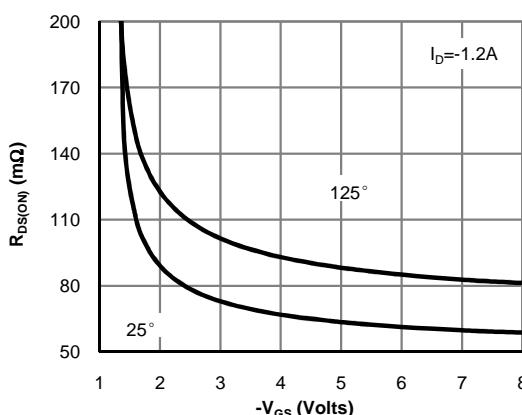
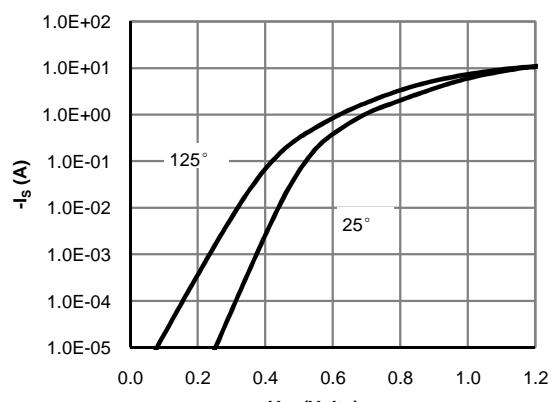
C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

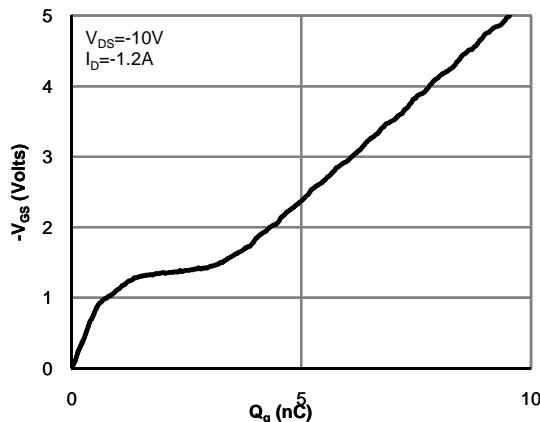
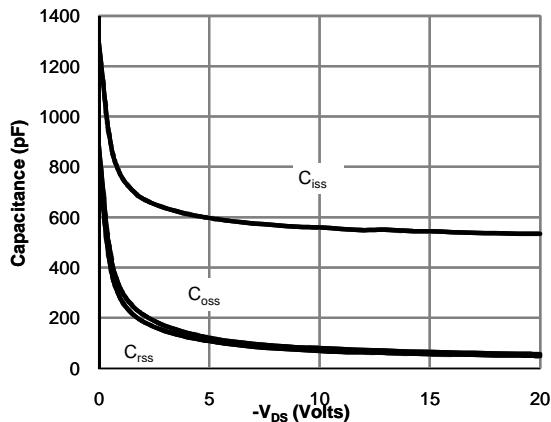
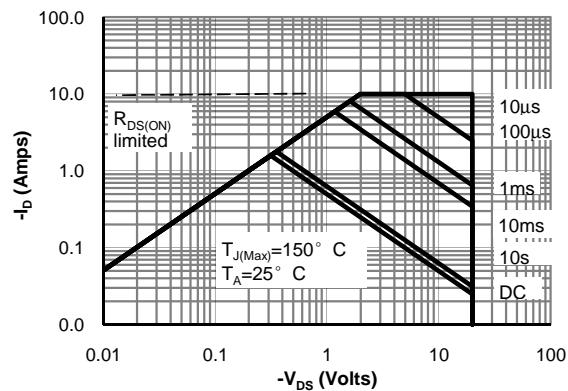
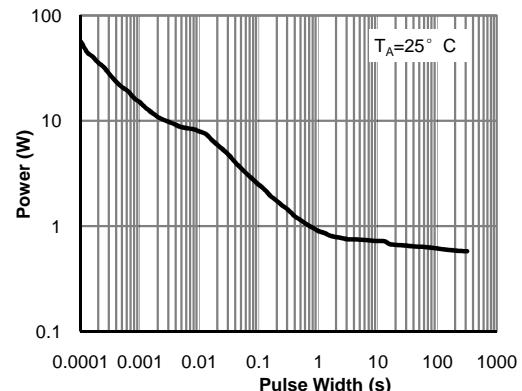
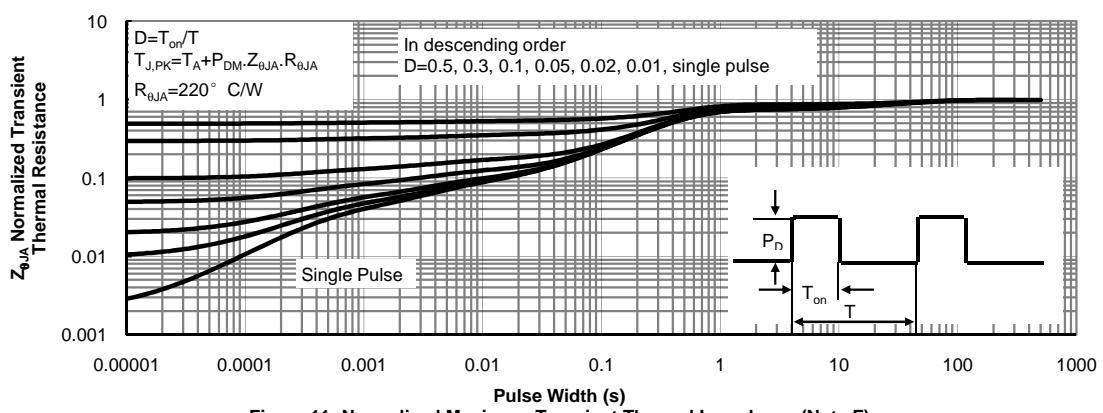
D. The R_{gJA} is the sum of the thermal impedance from junction to lead R_{gJL} and lead to ambient.

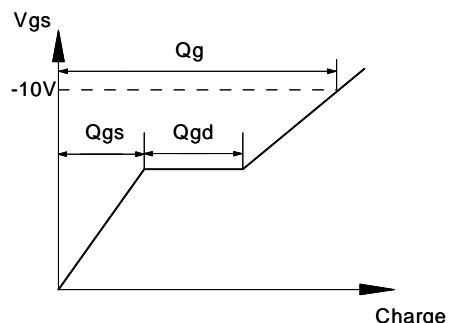
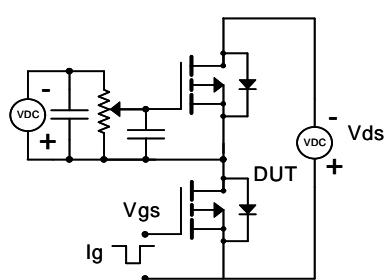
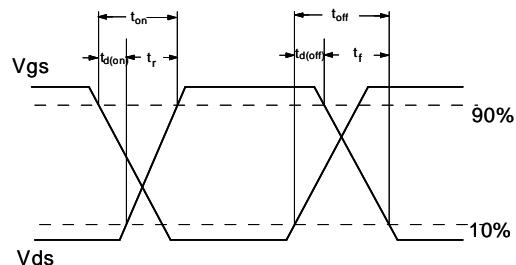
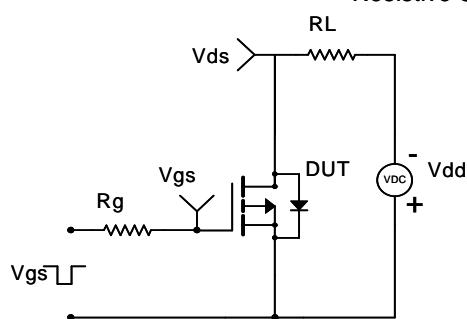
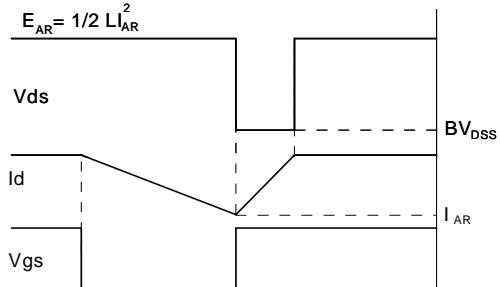
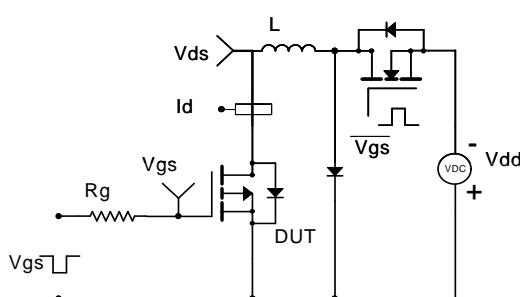
E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms
